

AGENDA

Symposium on Chemical-Mechanical Planarization August 12-15, 2007 Hilton Lake Placid Resort

Sunday, August 12:

- 12:00 - 5:00 P.M. Hotel Check-in and CAMP Registration
- 5:45 - 7:00 P.M. Cocktail Reception being held at The Olympic Regional Development, Olympic Center, 2634 Main Street, (No formal dinner provided)
- 6:15 - 7:30 P.M. Dancing Bears Lounge: For those arriving late – light hors d'oeuvres and a drink on CAMP

Monday, August 13:

- 7:00 - 8:00 A.M. Breakfast - Terrace Room

MEETING HELD IN MEDALLION ROOM

- 8:00 A.M. **S.V. Babu: Opening Remarks**

Session I

- 8:10 A.M. "Integration of Porous Low K Dielectrics: Materials & Metrology Challenges"
-- Mansour Moinpour, Intel Corporation.
- 8:35 A.M. "Damageless Cu-CMP for Porous Low-k/Cu Interconnects"
-- Seiichi Kondou, Selete
- 9:00 A.M. "EC(M)P - can we do it without the M" --Karl Hensen, BASF
- 9:25 A.M. "Comparison of the Planarization Technologies for the Next Generation"
-- Itsuki Kobata, Ebara Corporation
- 9:50 A.M. Coffee Break

Session II

- 10:15 A.M. "CMP Technology Trends and Markets" -- Karey Holland, Techcet Group, LLC
- 10:40 A.M. "Defectivity Mechanisms in CMP: Barrier and W CMP Processes"
-- Ajoy Zutshi, DA Nano
- 11:05 A.M. "The Effect of Consumables on CMP Defect Reduction" -- Picheng Huang, Praxair
- 11:30 A.M. "The Recent Advances in CMP Process Characterization Wafers"
-- Sookap Hahn, SKW
- 11:55 A.M. Discussion
- 12:00 P.M. Lunch - Terrace Room

Monday, August 13 Continued:

Session III

- 3:20 P.M. "Recent Advancements in Fixed Abrasive STI CMP"
-- John Gagliardi, 3M Company
- 3:45 P.M. "Cerium Oxide Manufacturing Process Control and Particle Morphology Effects on Defectivity for Future STI SMP Slurries" – David Merricks, Ferro Electronic
- 4:10 P.M. "Impact of Ceria Properties and CMP Parameters on STI CMP Performance"
-- Jo De Messemaeker, Umicore
- 4:35 P.M. "HARP CMP Removal Profile Alteration Through Slurry Dispense Position"
-- Matthew Smalley, IBM Albany
- 5:00 P.M. "Characterization of CMP Consumables: Opportunities and Challenges"
-- RK Singh, Entegris
- 5:30 – 7:00 P.M. [Poster Session/ Open Bar – Medallion Room \(note: day changed\)](#)
- 7:00 P.M. Dinner
- After Dinner Speaker: TBD

Tuesday, August 14:

7:00 - 8:00 A.M. Breakfast -Terrace Room

Session IV

- 8:05 A.M. "Enabling Solutions for 45 nm Node" -- Manabu. Tsujimura, Ebara Corporation
- 8:30 A.M. "Advanced CMP Consumables for 32nm Generation"
-- Masayuki Motonari, JSR Corporation
- 8:55 A.M. "Advanced Cu & Barrier CMP Slurry for 65-45nm Technology"
-- ShinodaTakashi, Hitachi Chemical Co., Ltd.
- 9:20 A.M. "Effect of Slurry pH on Ru CMP" -- Jin-Goo Park, Hanyang University
- 9:45 A.M. Coffee Break

Session V

- 10:15 A.M. "On the Relationship Between Contact Area Data and Polishing"
-- L. Borucki, Araca, Inc.
- 10:40 A.M. "The Impact of CMP Pad-Wafer Contact on Slurry Particle Flow at the Asperity Scale" Gregory Muldowney, Rohm and Haas

Tuesday, August 14 Continued:

- 11:05 A.M. "Investigation of CMP Pad Contact Characteristics by Computational Modeling and In-Situ Measurement"-- Bo Jiang, Carolina Elmufdi, and Gregory Muldowney, Rohm and Haas
- 11:30 A.M. "Effect of Concentric Slanted Groove Patterns on Slurry Flow During Copper CMP" D. Rosales-Yeomans University of Arizona
- 11:55 A.M. Discussion
- 12:00 P.M. Lunch – Terrace Room

Session VI

- 3:30 P.M. "LPC formation in Colloidal Silica based CMP Slurries" -- Scott Rader, Fujimi
- 3:55 P.M. "Origin of Various CMP Defects" -- Paul LeFevre, Innopad
- 4:20 P.M. "Advancements in Pad Conditioning for Tungsten Chemical Mechanical Planarization" --Tammy Engfer, 3M Company
- 4:45 P.M. "Study of Pad Surface Treatment for the Improvement of the Process Performance and the Productivity" -- Akira Isobe, Nitta-Haas Incorporated
- 5:10 P.M. Discussion
- 6:00 - 7:00 P.M. Reception at Lake Placid Club
- 7:00 P.M. Dinner at Lake Placid Club

Wednesday, August 15:

- 7:00 - 8:00 A.M. Breakfast - Terrace Room

Session VII

- 8:05 A.M. "Impact of Bevel Polish Cleaning on Wafer Surface Defects" -- Yoshikuni Tateyama, Toshiba Corporation
- 8:30 A.M. "In-situ Ellipsometric Study on the "Condensation" and "Cleaning" of a Metalorganic Copper Compound to/from Porous k Thin Films in Supercritical Carbon Dioxide" -- Eiichi Kondoh, University of Yamanashi
- 8:55 A.M. "In Situ Friction Coefficient Measurements During Metal CMP for Polishing Process Stabilize" -- Yohei Yamada Hitachi, Ltd.
- 9:20 A.M. "Development of Novel Post CMP Cleaning Solution" -- Sunny Xu, Anji Microelectronics, Shanghai China
- 9:45 A.M. "Developing Products for CMP Requires a Module-Level Approach, Peter Wrschka, ATMI, Inc. and Robert Rhoades, Entrepix, Inc
- 10:05 A.M. Break

Wednesday, August 15 Continued:

Session VIII

- 10:30 A.M. "Impact of Chloride Ions on Copper CMP" -- Intel
- 10:55 A.M. "Grind Silicon Wafer Polishing - Providing Industry Ultraflat Si Substrate"
-- Lily Yao, Strasbaugh
- 11:20 A.M. "Novel High Purity, pH Stable Colloidal Slurry"
-- B. Mullee, R. Small, S. Holland, and K. Holland, Silco
- 11:45 P.M. "CMP of Moisture Sensitive Materials"
-- Yuzhuo Li, CAMP
- 12:10 P.M. Closing Remarks, S.V. Babu, CAMP
- 12:15 P.M. Lunch - Terrace Room